


PRODUCT CHANGE NOTICE

1. TITLE IRHMS57160, Test Characteristics		2. DOCUMENT NUMBER FV5-C-16-005
		3. DATE November 5, 2015
4. MANUFACTURER AND ADDRESS International Rectifier 205 Crawford Street Leominster, MA 01453		5. MANUFACTURER PART NUMBER See below for IR Part Number
		6. BASE PART NA
		7. NATIONAL STOCK NUMBER (NSN) NA
8. CAGE 69210	9. EFFECTIVE DATE November 5, 2015	10. GOVERNMENT NUMBER NA
11. POINT OF CONTACT Manufacturer's Representative or Customer Service Representative (978) 534-5776		12. DRAWING NUMBER NA
		13. SPECIFICATION NUMBER MIL-PRF-19500
14. PRODUCT CHANGE This GIDEP PCN is to announce a change in the electrical characteristics for the following International Rectifier Part No listed below. This change is also coordinated with MIL-PRF-19500/698 change from revision E to F. IRHMS57160 (JANSR2N7471T1) 100V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a Low Ohmic TO-254AA package Electrical Characteristics @ Tj = 25°C, RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A Change RDS(on) Max limit from 0.013 Ω to 0.014 Ω Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation RDS(on) [Static Drain-to-Source On-State Resistance], with test condition of VGS = 12V, ID = 45A For up to 500K Rads(Si), Low-Ohmic TO-254 only Change RDS(on) Max limit from 0.013 Ω to 0.014 Ω For 1000K Rads (Si), Low-Ohmic TO-254 only Change RDS(on) Max limit from 0.014 Ω to 0.015 Ω Reference: IR Datasheet PD-95889		
		16. APPROVING GOVERNMENT ACTIVITY
17. GIDEP REPRESENTATIVE Paul Hebert	18. SIGNATURE 	19. DATE November 5, 2015

